

# True Kelvin CMOS Test Structure to achieve Accurate and Repeatable DC Wafer-Level Measurements for Device Modelling Applications

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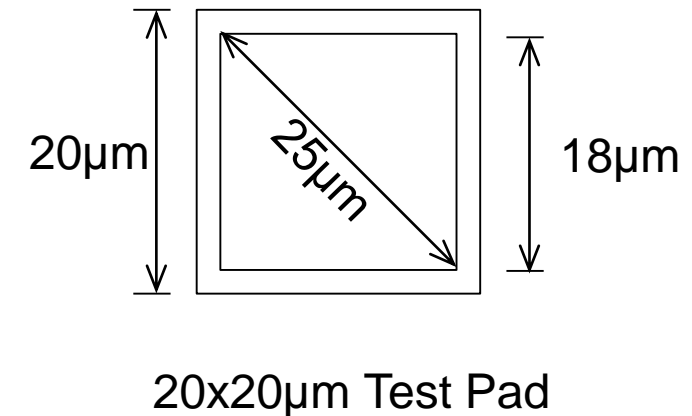
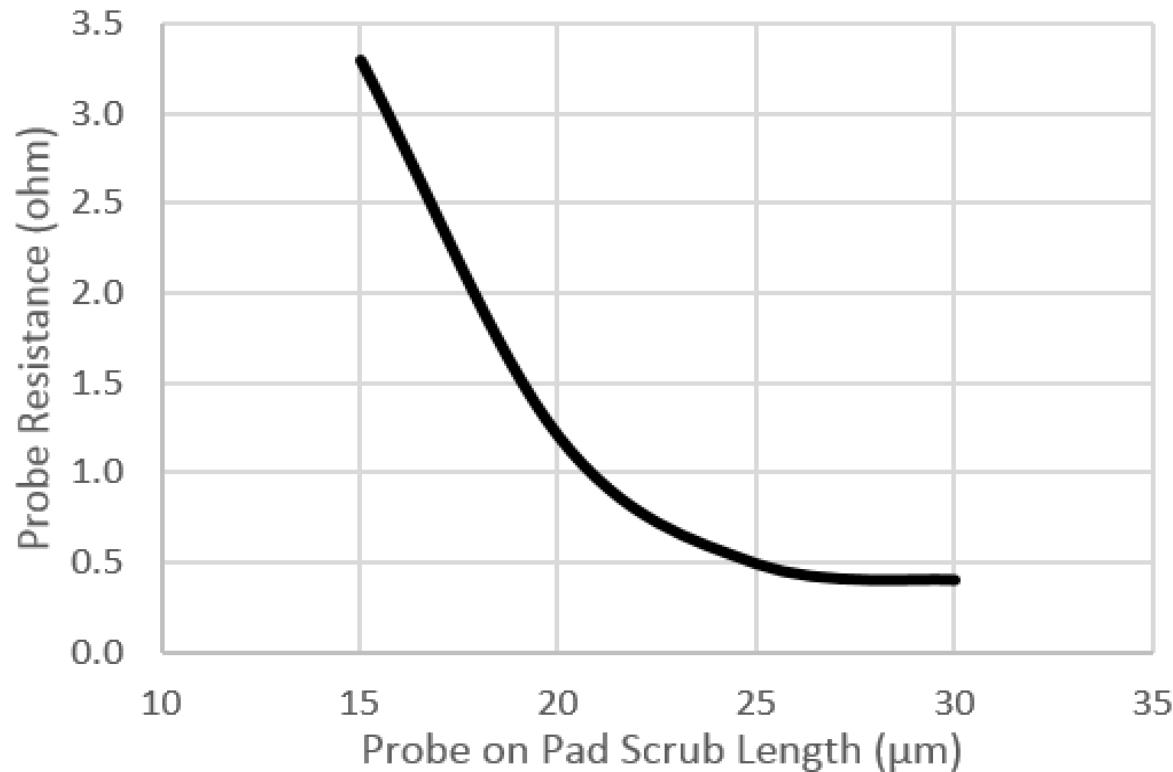
# ◆ Agenda

- Challenges for Wafer-Level DC Modeling Measurements
- Typical Probe Contact Resistance vs Scrub Length
- Proposed Test Structure Design
- Experimental Setup
- Characterizing Probe  $R_C$  on Test Pads
- Results & Discussions for NMOS measurements
- Recommendations
- Conclusions

## ◆ Challenges for Wafer-Level DC modeling measurements

- Achieve Accurate & Repeatable measurements at Different Temperatures
- Reduction in Device Channel Resistance  $R_{ds}$ 
  - Probe parasitic resistances are Not Negligible!
- Reduction in Pad size (30x30 $\mu\text{m}$  to 20x20 $\mu\text{m}$ )
  - Smaller tips = large contact resistance
  - Continue using low cost Cantilever probecards requiring longer probe scrub
- How to ensure low Probe  $R_C$  at different test temperature?
  - Probe on fresh metallization for 3 times or more on pads  $\leq$  30x30 $\mu\text{m}$
- Cu Backend Interconnects underneath Al capped pads
  - When exposed, underlying Cu oxidizes rapidly at high temperature
  - Test Wafers goes through thermal cycles, how to repeat the test results 1 year later?
- Wider Thermal test range
  - From -40 to 125 Deg C to -50 to 175 Deg C

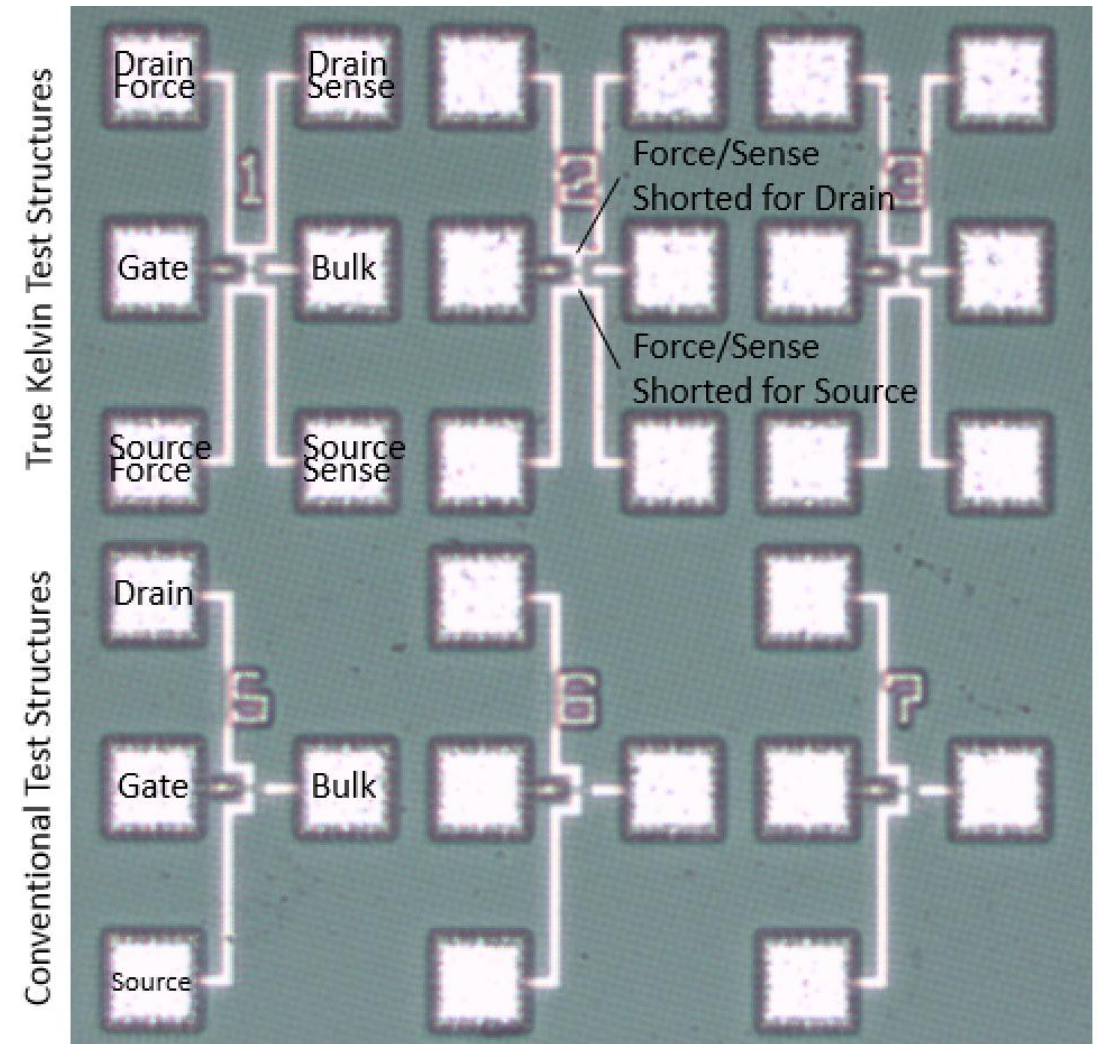
# ◆ Typical Cantilever Probe $R_C$ vs Scrub Length



- $> 25\mu\text{m}$  scrub needed for low probe  $R_C$
- Challenging to support 20x20μm pads (Diagonally only 25μm)
  - How to get sufficient scrub, 3 times on the same pad?

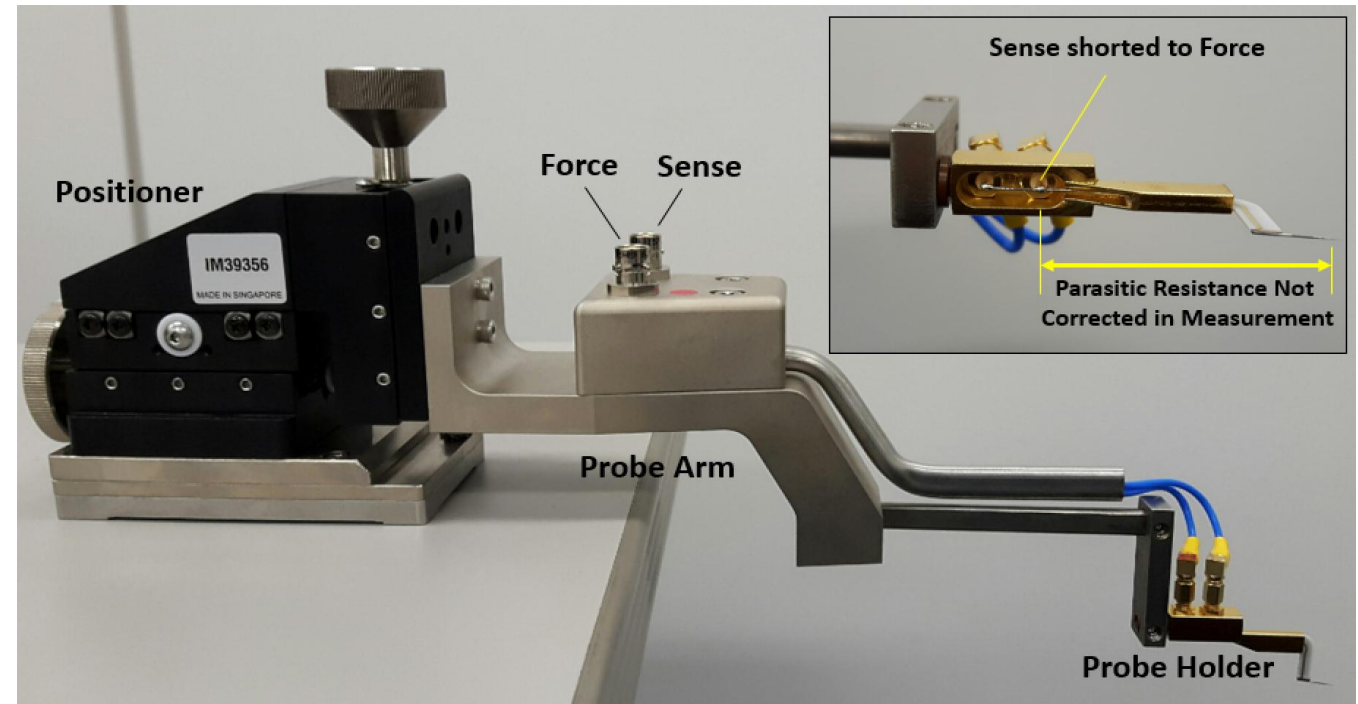
# ◆ Proposed Test Structure Design

- 60nm CMOS devices
- Conventional Test Structure
  - 4 test pads
  - Parasitic Resistances not corrected.
- Probe Kelvin Test Structure
  - 6 test pads
  - Source/Drain with additional Sense (Test Leads and Pads)
  - Parasitic Resistances are corrected.
    - Post layout parasitics simulations



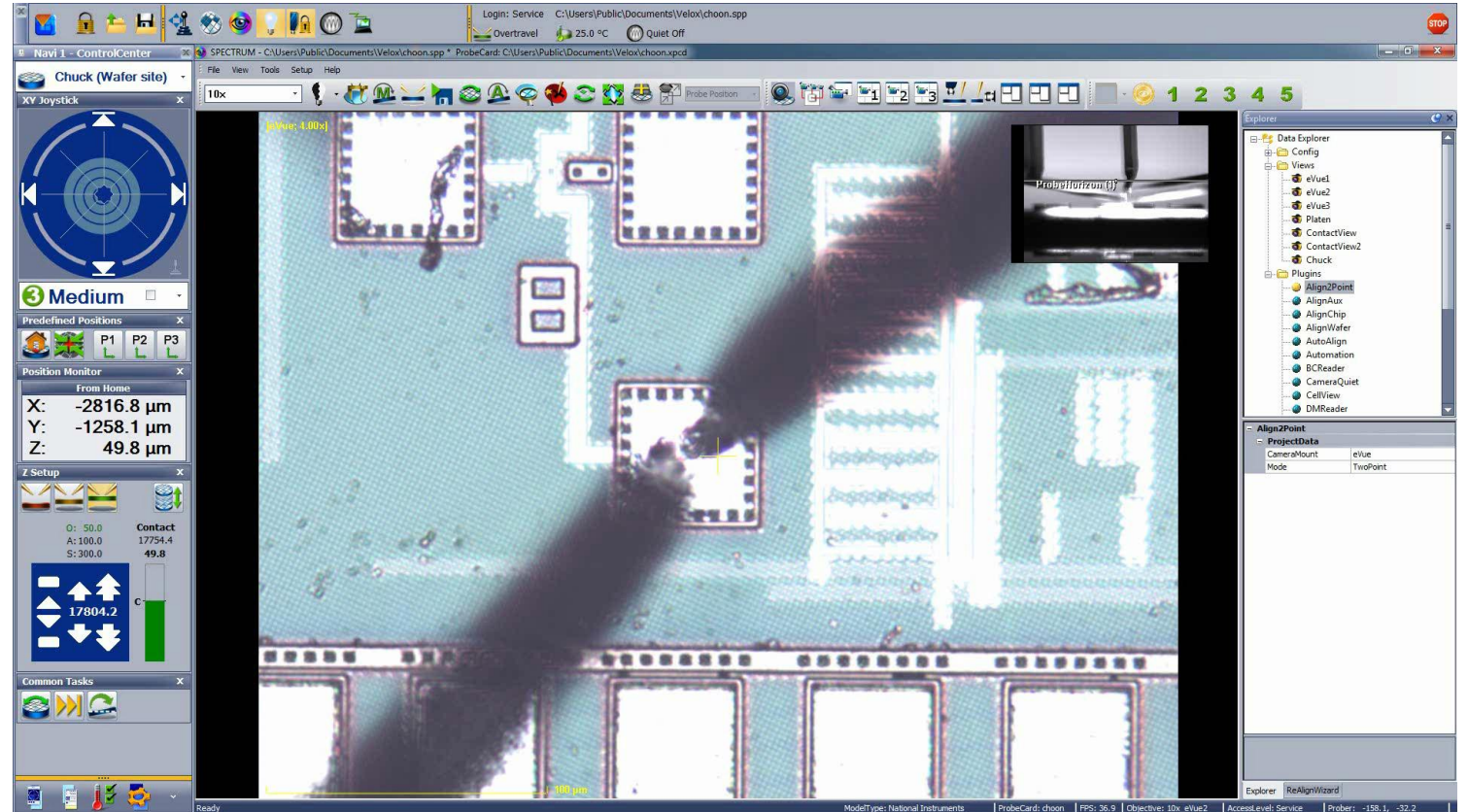
## ◆ Experimental Setup

- Test Wafer with 60nm CMOS devices
- Cascade Shielded Probe Station
- Keysight Semiconductor Parametric Analyzer B1500
- Single Probe positioner used instead of probecard for test flexibilities



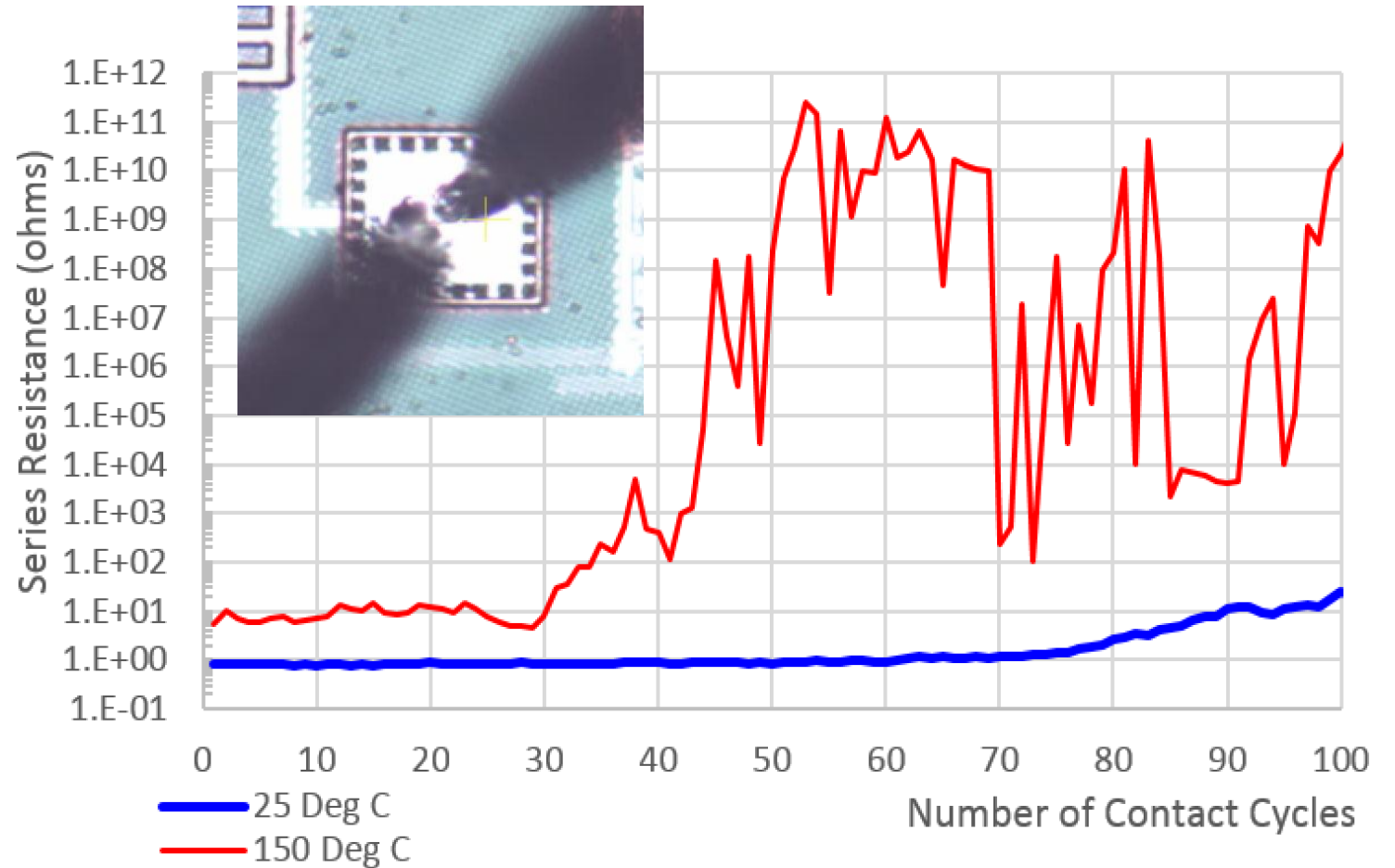
# ◆ Characterizing Probe $R_C$ on Single Test Pad

- 2 probes on same pad
- 30 $\mu$ m probe scrub
  - Ensure low  $R_C$
- 100 contact cycles
  - Re-probing on the same spot
  - Worst-case testing



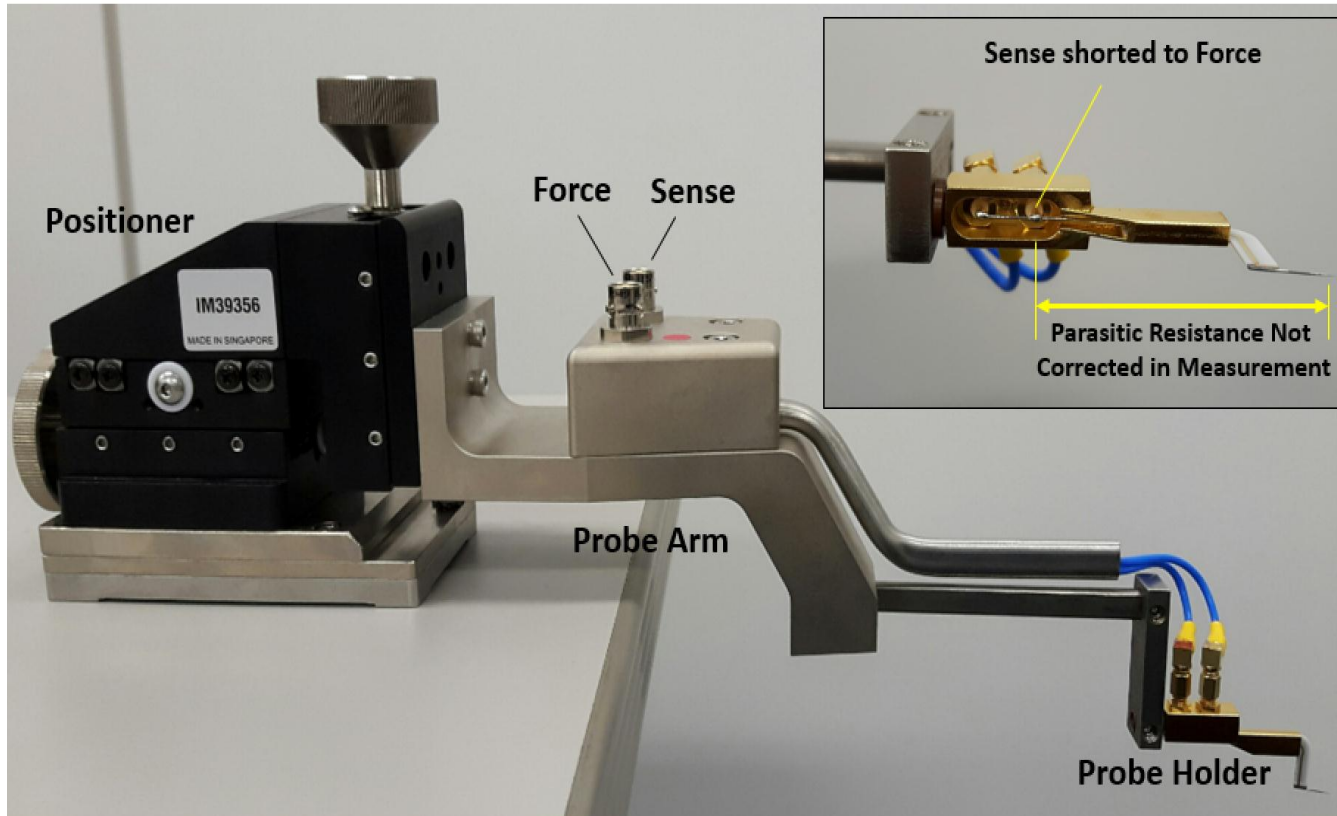
# ◆ Characterizing Probe $R_C$ on Single Test Pad

- 25 Deg C Test
  - 1<sup>st</sup> 75 Contact Cycles
    - 0.8 to 1 ohms
  - 100<sup>th</sup> contact cycles
    - 20 ohms
- 150 Deg C Test
  - Replaced Tips & Check Probe  $R_C$  at 25°C
  - 1<sup>st</sup> 30 Contact Cycles
    - about 5 ohms
  - 43<sup>rd</sup> contact cycle, underneath Cu oxidizes, resulting in open circuit





# ◆ Characterizing Probe RC on Test Pads

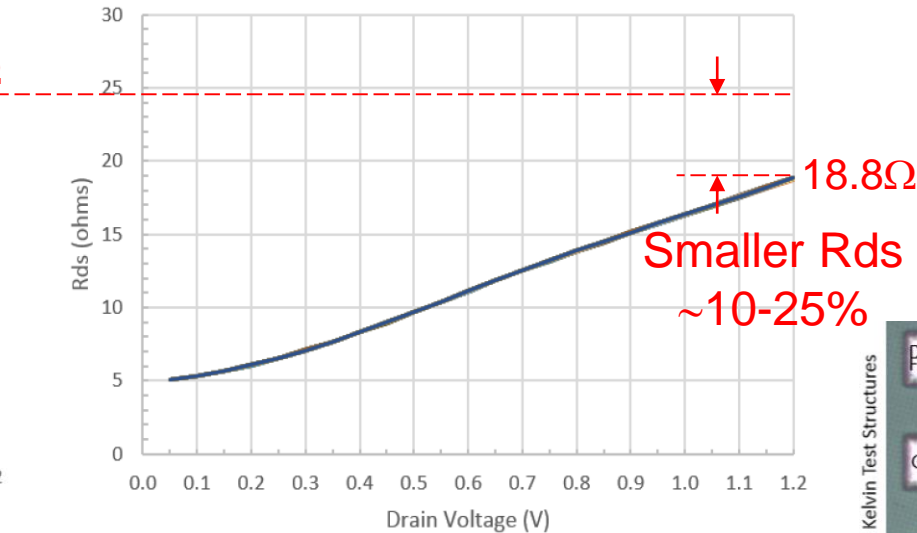
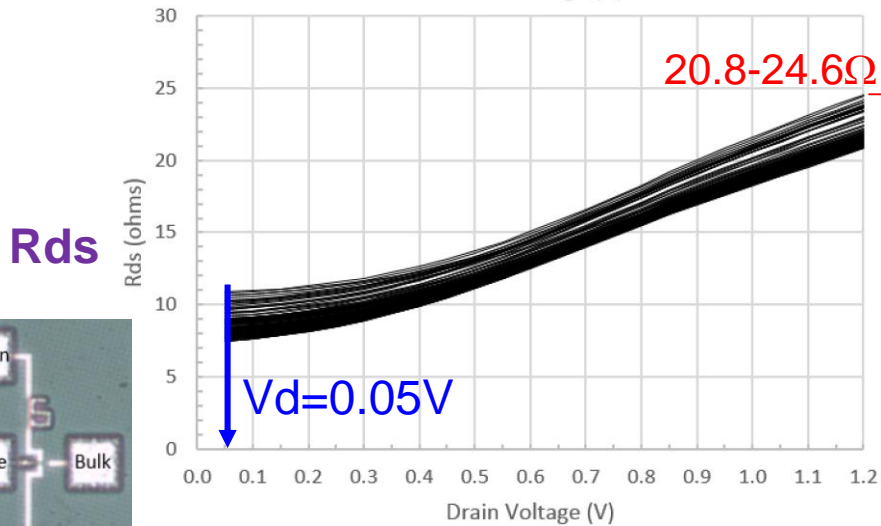
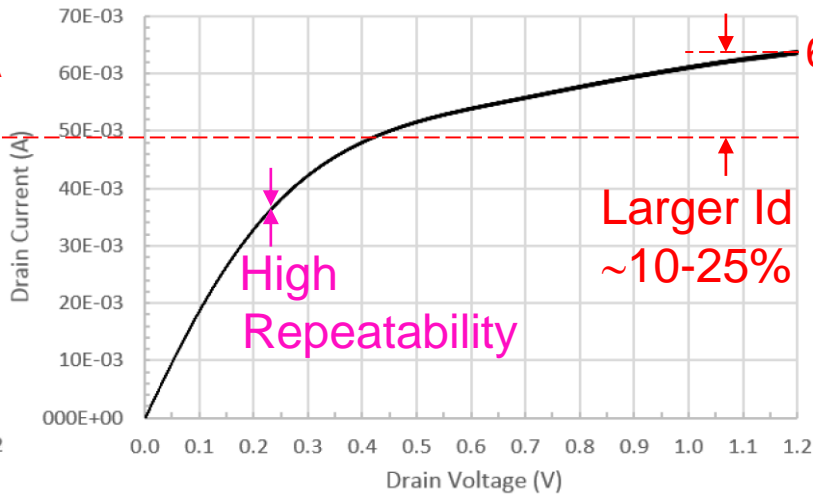
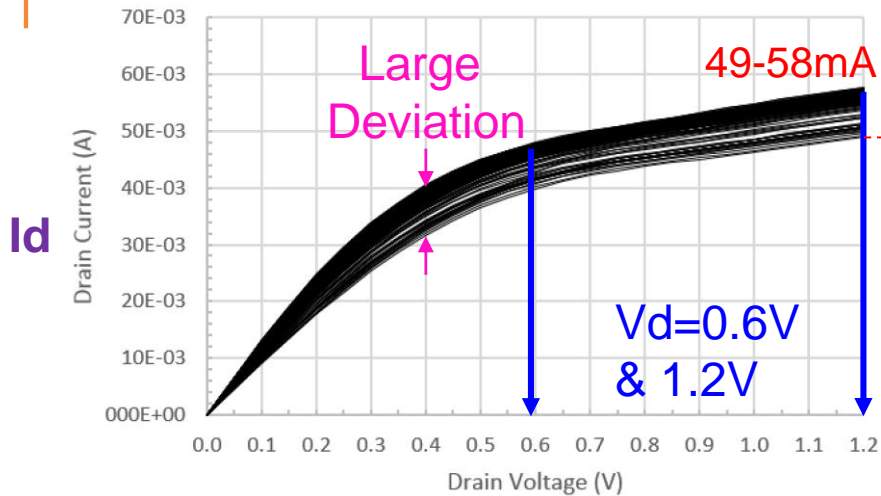


- Each Probe Parasitic Resistance
  - @ 25 Deg C = 0.4 ohms
  - @ 150 Deg C = 2.5 ohms
- Too large for advanced devices with decreasing Rds.
- Probecard will also have such large parasitic resistance if sense lines are not close enough to the device terminals.

The background features a light blue and white color scheme with a grid pattern. Overlaid on this are several faint, semi-transparent technical diagrams and graphs. These include circular gauges with arrows, bar charts with numerical values like 0.2, 0.4, 0.6, and 1, and various geometric shapes and lines. A prominent orange horizontal line runs across the middle of the slide, with a vertical orange line intersecting it on the left side, forming a crosshair that points towards the main title.

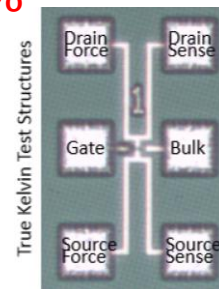
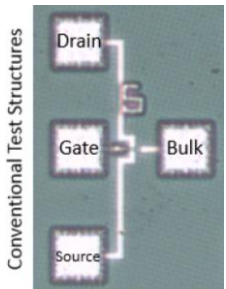
# ◆ Results & Discussions for NMOS Measurements

# Id & Rds vs Vd @ Vg=1.2V, 25°C, 100 contact cycles for 60nm NMOS



**Conventional Test Structure**

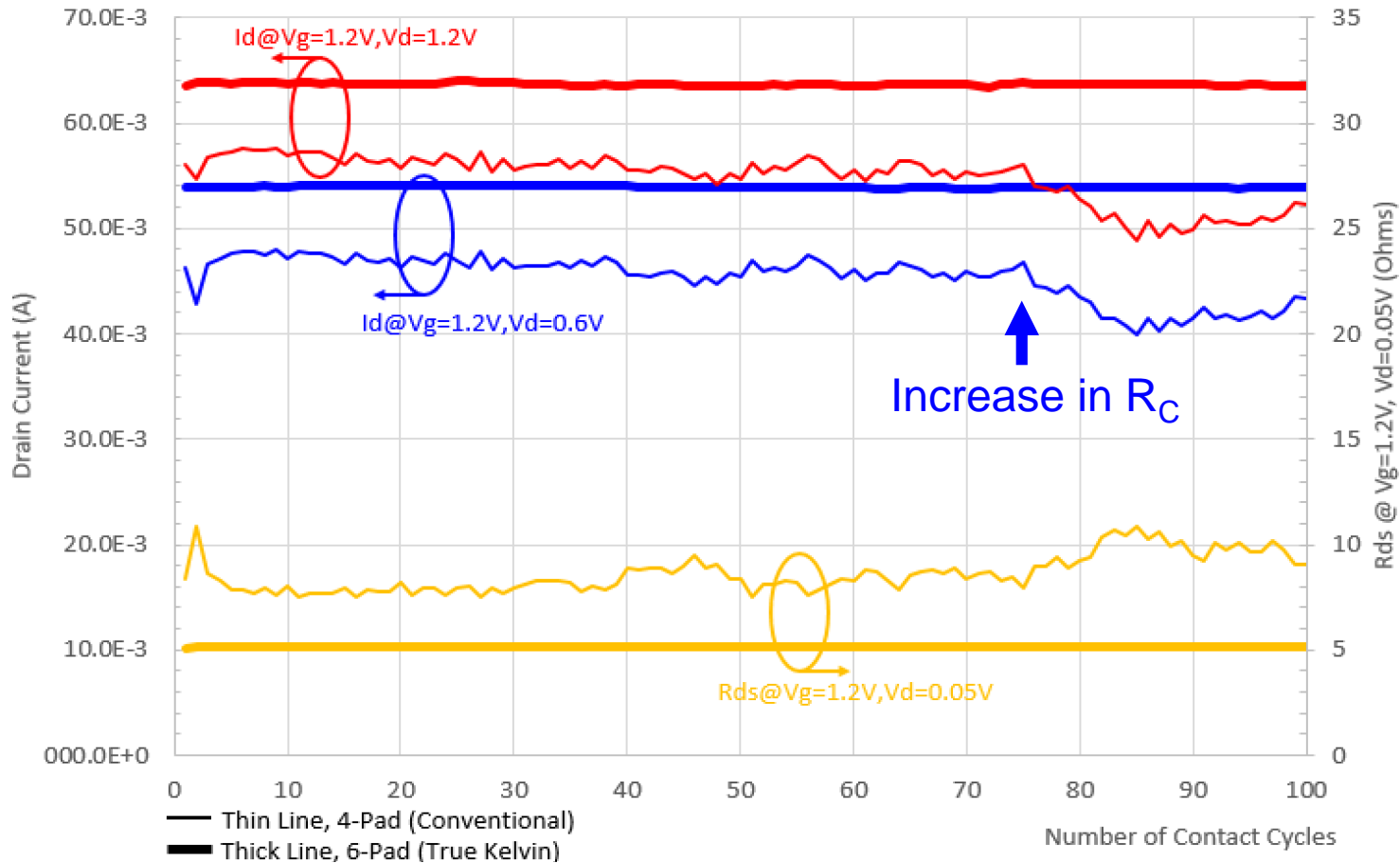
**Proposed Kelvin Test Structure**



## ● Kelvin Test structure

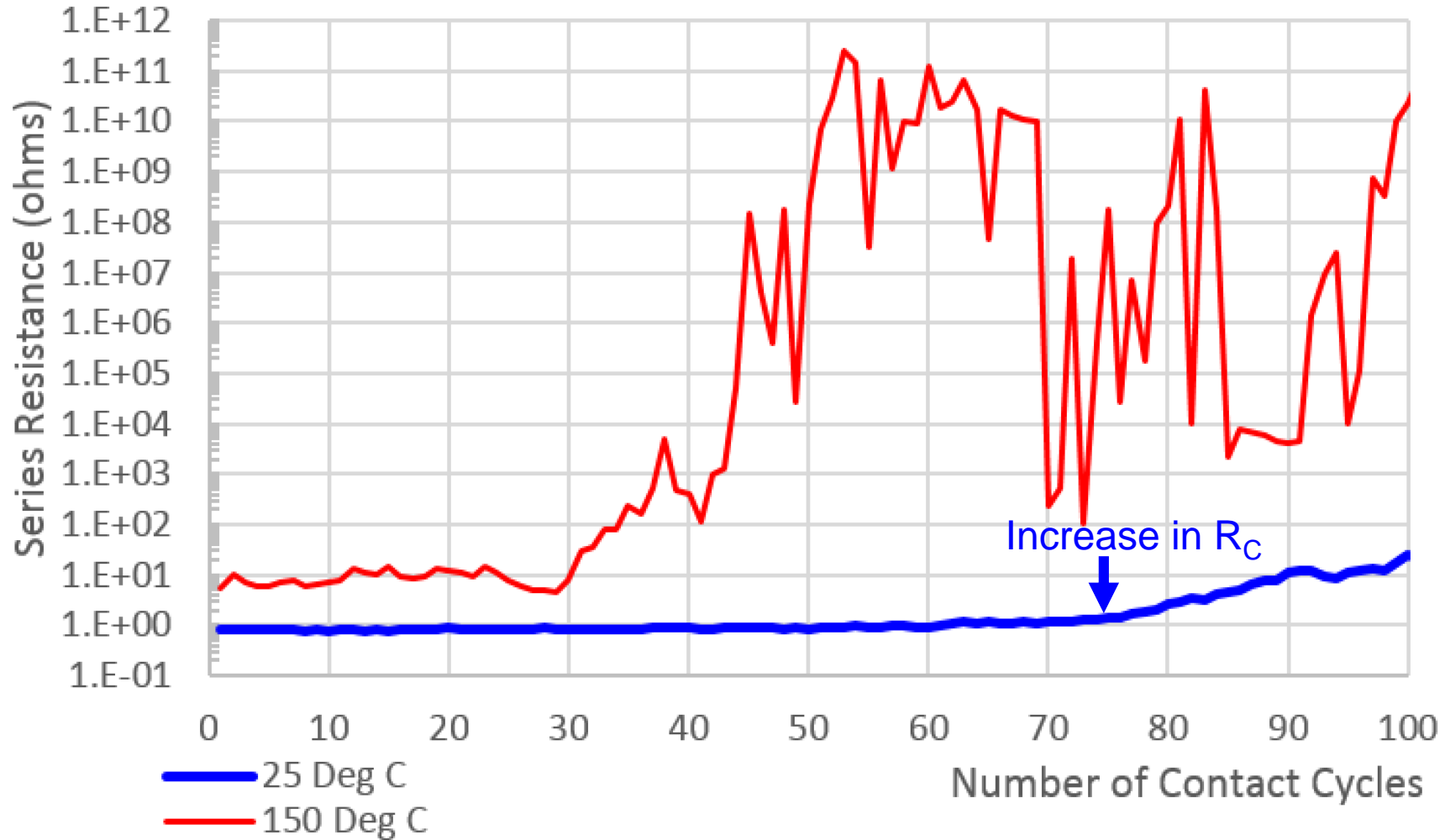
- Accurate and very repeatable results over 100 Contact Cycles
- Probe parasitics are corrected
- Larger Id & Smaller Rds

# ◆ Id & Rds vs 100 Contact Cycles @ 25°C for 60nm NMOS

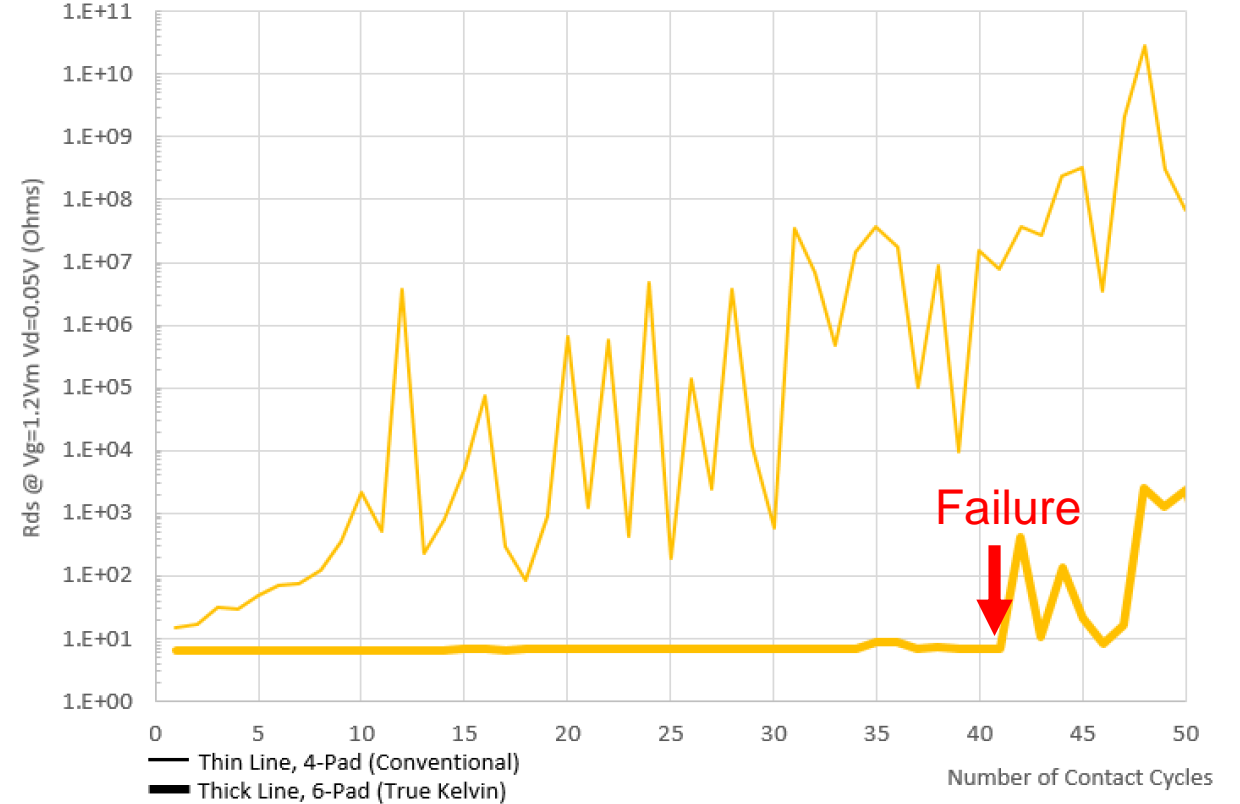
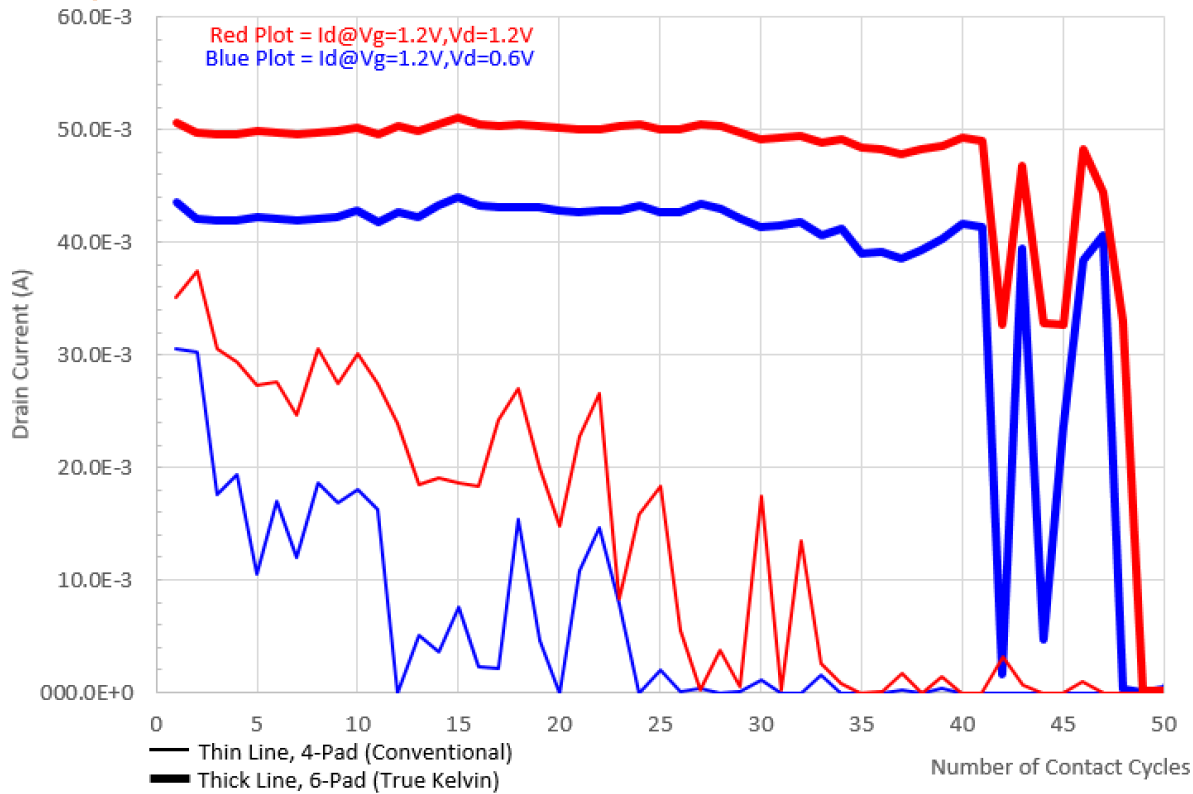


- Kelvin vs Conventional Test Structure
  - Measured Id & Rds is extremely stable & repeatable throughout 100 contact cycles.
  - Sense line of B1500 is able to correct and mitigate the increase in Rc.
  - Probe tip cleaning not required.

# ◆ Characterizing Probe $R_C$ on Single Test Pad



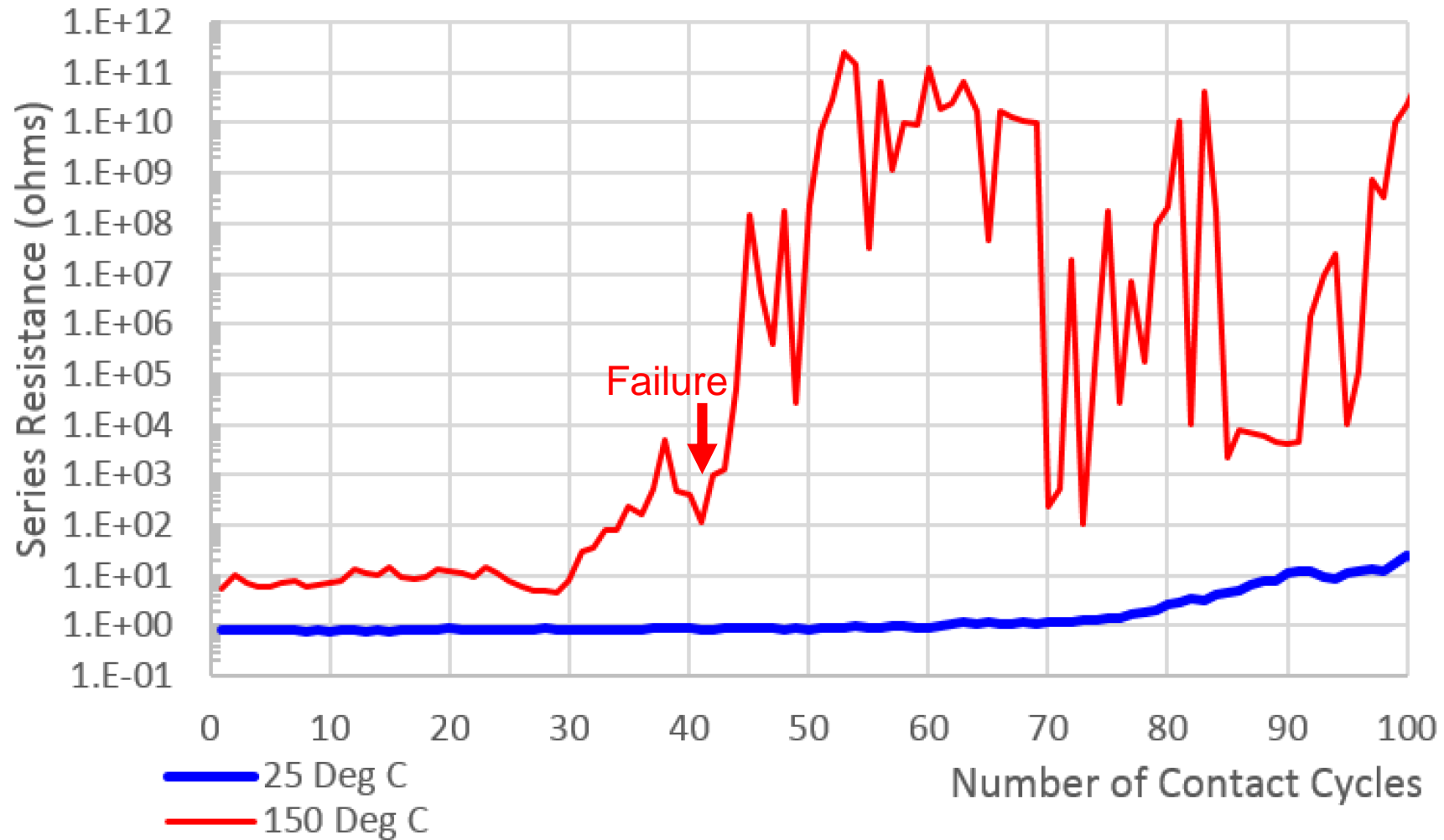
# ◆ Id & Rds vs 50 Contact Cycles @ 150°C for 60nm NMOS



## ● Kelvin Structure

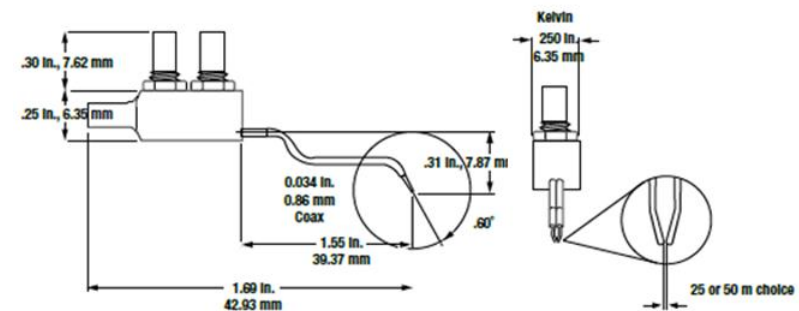
- 1<sup>st</sup> Contact Cycle, Id larger by 30%, Rds much smaller
- 43<sup>rd</sup> Contact Cycle, failure due to underlying Pad Cu fully oxidized

# ◆ Characterizing Probe $R_C$ on Single Test Pad



# ◆ Recommendations


- Recommended Test Sequence:
  - Hot Temp  $\Rightarrow$  Room Temp  $\Rightarrow$  Cold Test
  - Test Structures are not probed yet, minimize exposed Cu oxidation
- Adopt an Inert Test Environment
- Adopt Thicker Al. top cap layer
- Adopt Larger Pad (Fresh Metallization)
- Invest in Vertical Probe Card with frequent Tip Cleaning Cycles
  - Possible to minimize probe parasitics
  - Test Leads not corrected, affects Model accuracy
- Invest in True Kelvin Probe Tips
  - Bigger or Longer pads to accommodate 2 Tips
  - Test Leads not corrected, affects Model accuracy
- Adopt True Kelvin Test structure





## ◆ Conclusions – Adopt True Kelvin Test Structure as it...

- Corrects Probe parasitic resistances (Vary with Temperature).
- Corrects Test Leads parasitic resistances
  - Models should not account for test leads).
- Minimizes Retest & Revalidation
- Allows repeated probing of Same Device without Accuracy Degradation.
  - Example: Retesting of Golden Wafer for Model development after 1 year of model release
- Allows handling of small test pads  $< 30 \times 30 \mu\text{m}$  with cantilever probecard
  - Using smaller probe scrub and smaller probe tips
- No Probe Tip Cleaning required!
  - if B1500 has sufficient voltage headroom to correct for Parasitic Resistances.
- Mitigates  $\uparrow R_C$  due to oxidation of underlying Cu underneath test pads.
- Though larger layout, provides Accurate Results with Lower Cost of Test

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◆ Thank You!  
Questions?